

AMENDMENTS TO THE CLAIMS

Please amend the claims as shown below. A complete listing of all pending claims is presented.

1. (Currently Amended) A semiconductor device comprising:

a semiconductor mesa portion formed on a substrate, including a stack of at least a sub-collector layer, a collector layer, a base layer, and an emitter layer formed in narrower region compared with said base layer, and functioning as an active region of a bipolar transistor an emitter cap layer and said emitter layer forming an emitter mesa portion EM, the base layer and the collector layer forming a base mesa portion BM, the sub-collector layer formed with a sub-collector mesa portion SM for isolating elements, and said collector layer is formed connected with the sub-collector layer ;

a base contact pad mesa portion PSM formed on said substrate apart from said semiconductor mesa portion and formed with a height the same as the height of the top surface of said base layer and including a layer formed by the same layer as the collector layer, a layer formed by the same layer as the base layer, and layer formed by the same layer as the sub-collector layer; [and]

a conductive layer formed integrally with a base electrode formed connected to said base layer at part of a region of formation of said base layer other than the region of formation of said emitter layer, a base contact pad electrode formed above said base contact pad mesa portion in a region other than near the edges of the top surface of said base contact pad mesa portion, and an interconnect for connecting said base electrode and said base contact pad electrode, wherein an insulating film is formed below said conductive layer between said semiconductor mesa portion and said base contact pad mesa portion; and

an insulating film formed over said heterojunction bipolar transistor HBT.

2. (Canceled)

3. (Original) A semiconductor device as set forth in claim 1, wherein the area under said conductive layer between said semiconductor mesa portion and said base contact pad mesa portion forms a space.

4. (Canceled)

5. (Canceled)

6. (Original) A semiconductor device as set forth in claim 1, wherein a distance between said semiconductor mesa portion and said base contact pad mesa portion is 1 to 5 μm .

7. (Canceled)

8. (Cancelled)

9. (Cancelled)

10. (Cancelled)

11. (Cancelled)

12. (Cancelled)

13. (Currently amended) A semiconductor device comprising:

a semiconductor mesa portion formed on a substrate, including a stack of at least a collector layer, a base layer, and an emitter layer formed in narrower region compared with said base layer, and functioning as an active region of a heterojunction bipolar transistor (HBT);

a base contact pad mesa portion formed on said substrate apart from said semiconductor mesa portion and formed with a height the same as the height of the top surface of said base layer; and

a conductive layer formed integrally with a base electrode formed connected to said base layer at part of a region of formation of said base layer other than the region of formation of said emitter layer, a base contact pad electrode formed above said base contact pad mesa portion in a region other than near the edges of the top surface of said base contact pad mesa portion, and an interconnect for connecting said base electrode and said base contact pad electrode, wherein said base electrode is formed in a region other than the region of formation of said emitter layer and other than near the edges of said base layer,

wherein a distance between said semiconductor mesa portion and said base contact pad mesa portion is 1 to 5 μm to reduce the area of the HBT while preventing damage to the interconnect having a thickness of about 0.2 to 0.5 μm .

14. (Previously presented) A semiconductor device as set forth in claim 13, wherein the surface layer of said base contact pad mesa portion is formed by the same layer as said base layer.

15. (Previously presented) A semiconductor device as set forth in claim 13, wherein the area under said conductive layer between said semiconductor mesa portion and said base contact pad mesa portion forms a space.

16. (Cancelled)

17. (Canceled)